a getter region overlying at least part of the light-blocking region and extending no more than partially laterally across the light-emissive region; and

a perforated electrically non-insulating layer overlying at least part of the getter region or/and at least part of the light-emissive region.

- 2. (Original) A structure as in Claim 1 wherein an opening extends through the getter region generally laterally where the light-emissive region overlies the plate.
- 3. (Original) A structure as in Claim 1 wherein the light-blocking region is largely absorptive of visible light which passes through the plate and impinges on the light-blocking region.
- 4. (Original) A structure as in Claim 1 wherein the non-insulating layer is electrically conductive.
- 5. (Original) A structure as in Claim 4 further including means for applying a selected electrical potential to the non-insulating layer during operation of the structure.
- 6. (Original) A structure as in Claim 1 wherein the non-insulating layer overlies at least the light-emissive region.
- 7. (Original) A structure as in Claim 6 wherein the non-insulating layer is generally reflective of visible light.
- 8. (Original) A structure as in Claim 1 wherein the non-insulating layer overlies the getter and light-emissive regions.
- 9. (Canceled)
- 10. (Original) A structure as in Claim 1 wherein the light-emissive region emits light upon being struck by electrons of sufficiently high energy.
- 11. (Original) A structure as in Claim 1 wherein the light-blocking region laterally surrounds the light-emissive region.

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- 12. (Original) A structure as in Claim 1 wherein the light-blocking region extends further away from the plate than the light-emissive region.
- 13. (Original) A structure as in Claim 1 wherein the getter region comprises at least one of aluminum, titanium, vanadium, iron, zirconium, niobium, molybdenum, barium, tantalum, tungsten, and thorium.
- 14. (Original) A structure as in Claim 1 wherein the getter region comprises a titanium-zirconium alloy.
- 15. (Original) A structure as in Claim 1 wherein the getter region consists largely of only a single atomic element.
- 16. (Previously amended) A structure as in Claim 15 wherein the single atomic element is one of aluminum, titanium, vanadium, iron, zirconium, niobium, molybdenum, barium, tantalum, tungsten, and thorium.
- 17. (Original) A structure as in Claim 1 further including an additional region situated over at least part of the light-blocking region and under at least part of the non-insulating layer.
- 18. (Original) A structure as in Claim 17 wherein the additional region is situated over at least part of the getter region.
- 19. (Original) A structure as in Claim 17 wherein the additional region is largely impervious to passage of gases.
- 20. (Previously amended) A structure as in Claim 17 wherein the additional region is largely impervious to passage of electrons.
- 21. (Original) A structure as in Claim 17 wherein the additional region covers all, or nearly all, of the light-blocking region along its outside surface.

- 22. (Original) A structure as in Claim 1 further including a protective layer situated over at least part of the getter region and under the non-insulating layer, the protective layer lying between at least part of the getter region and at least part of the light-emissive region.
- 23. (Original) A structure as in Claim 22 wherein the protective layer is largely impervious to passage of electrons.
- 24. (Original) A structure as in Claim 1 wherein the light-blocking region has a remote surface most distant from the plate, the getter region overlying at least part of the remote surface of the light-blocking region.
- 25. (Original) A structure as in Claim 24 wherein the getter region overlies largely all of the remote surface of the light-blocking region.
- 26. (Original) A structure as in Claim 1 wherein the getter region extends at least partway down into the opening in the light-blocking region.
- 27. (Original) A structure as in Claim 1 wherein the getter region extends substantially all the way down into the opening in the light-blocking region.
- 28. (Original) A structure as in Claim 1 wherein the getter region extends into the opening in the light-blocking region and partially over the plate at the bottom of the opening in the light-blocking region.
- 29. (Original) A structure as in Claim 1 further including a device for emitting electrons which strike the light-emissive region and cause it to emit light.
- 30. (Previously amended) A structure as in Claim 29 wherein the electron-emitting device includes a further getter region situated at least partially in an active electron-emitting portion of the electron-emitting device.

- 31. (Previously amended) A structure comprising:
  - a plate;
- a light-blocking region overlying the plate and being generally non-transmissive of visible light, an opening extending largely through the light-blocking region above where the plate is generally transmissive of visible light;
- a light-emissive region overlying the plate and situated at least partially in the opening in the light-blocking region;
- an electrically non-insulating layer overlying at least part of the light-blocking region; and
- a getter region overlying at least part of the non-insulating layer above at least part of the light-blocking region, an opening extending largely through the getter region generally laterally where the light-emissive region overlies the plate.
- 32. (Original) A structure as in Claim 31 wherein the light-blocking region is largely absorptive of visible light which passes through the plate and impinges on the light-blocking region.
- 33. (Original) A structure as in Claim 31 wherein the non-insulating layer is electrically conductive.
- 34. (Original) A structure as in Claim 33 further including means for applying a selected electrical potential to the non-insulating layer during operation of the structure.
- 35. (Original) A structure as in Claim 31 wherein the non-insulating layer also overlies at least part of the light-emissive region.
- 36. (Original) A structure as in Claim 35 wherein the non-insulating layer is generally reflective of visible light.
- 37. (Original) A structure as in Claim 31 wherein the light-emissive region emits light upon being struck by electrons of sufficiently high energy.

- 38. (Original) A structure as in Claim 31 wherein the light-blocking region extends further away from the plate than the light-emissive region.
- 39. (Original) A structure as in Claim 31 further including a device for emitting electrons which strike the light-emissive region and cause it to emit light.
- 40. (Previously amended) A structure as in Claim 39 wherein the electron-emitting device includes a further getter region situated at least partially in an active electron-emitting portion of the electron-emitting device.
- 41. (Previously amended) A structure comprising:
  - a plate;
  - an electron-emissive element overlying the plate;
  - a support region overlying the plate; and
- a getter region overlying at least part of the support region, a composite opening extending through the getter and support regions generally laterally where the electron-emissive element overlies the plate, the composite opening comprising (a) an opening through the getter region and (b) an opening through the support region.
- 42. (Original) A structure as in Claim 41 further including a dielectric layer overlying the plate below the support region, the electron-emissive element situated mostly in an opening in the dielectric layer.
- 43. (Original) A structure as in Claim 41 further including a control electrode for selectively extracting electrons from the electron-emissive element or for selectively passing electrons emitted by the electron-emissive element, the control electrode overlying the plate and having an opening through which the electron-emissive element is exposed.
- 44. (Original) A structure as in Claim 43 further including electrically insulating material extending over at least part of the control electrode.
- 45. (Original) A structure as in Claim 43 wherein the support region extends further away from the plate than the control electrode.

- 46. (Original) A structure as in Claim 41 wherein the support region comprises a base focusing structure of an electron-focusing system for focusing electrons emitted by the electron-emissive element.
- 47. (Original) A structure as in Claim 46 wherein the electron-focusing system includes an electrically non-insulating focus coating which comprises the getter region, whereby at least part of the focus coating overlies the base focusing structure.
- 48. (Original) A structure as in Claim 46 wherein the electron-focusing system includes an electrically non-insulating focus coating situated over at least part of the getter region, an opening extending through the focus coating at least generally laterally where the electron-emissive element overlies the plate.
- 49. (Original) A structure as in Claim 48 wherein the focus coating is perforated.
- 50. (Previously amended) A structure as in Claim 46 wherein the electron-focusing system includes an electrically non-insulating focus coating situated over at least part of the base focusing structure and under at least part of the getter region.
- 51. (Original) A structure as in Claim 41 wherein the support region comprises a control electrode for selectively extracting electrons from the electron-emissive element or for selectively passing electrons emitted by the electron-emissive element.
- 52. (Original) A structure as in Claim 51 further including a raised section overlying the plate and extending over at least part of the control electrode, the getter region being exposed through or/and situated in an opening in the raised section.
- 53. (Original) A structure as in Claim 51 wherein the getter region focuses electrons emitted by the electron-emissive element.
- 54. (Original) A structure as in Claim 53 wherein the getter region comprises electrically non-insulating material substantially electrically decoupled from the control electrode.

- 55. (Original) A structure as in Claim 54 further including electrically insulating material situated between at least part of the control electrode and at least part of the getter region.
- 56. (Original) A structure as in Claim 41 wherein the getter region comprises at least one of aluminum, titanium, vanadium, iron, zirconium, niobium, molybdenum, barium, tantalum, tungsten, and thorium.
- 57. (Original) A structure as in Claim 41 wherein the getter region consists largely of only a single atomic element.
- 58. (Original) A structure as in Claim 57 wherein the single atomic element is one of aluminum, titanium, vanadium, iron, zirconium, niobium, molybdenum, barium, tantalum, tungsten, and thorium.
- 59. (Original) A structure as in Claim 41 further including a device for emitting light upon being struck by electrons emitted by the electron-emissive element.
- 60. (Previously amended) A structure as in Claim 59 wherein the light-emitting device includes a further getter region situated at least partially in an active light-emitting portion of the light-emitting device.
- 61. (Previously amended) A structure comprising:

a plate;

an electron-emissive element overlying the plate;

a control electrode for selectively extracting electrons from the electron-emissive element or for selectively passing electrons emitted by the electron-emissive element, the control electrode overlying the plate and having an opening through which the electron-emissive element is exposed; and

a getter region overlying at least part of the control electrode and contacting, or connected by directly underlying electrically insulating material to, the control electrode.

62. (Original) A structure as in Claim 61 wherein an opening extends through the getter region generally laterally where the electron-emissive element overlies the plate.

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- 63. (Original) A structure as in Claim 61 further including a dielectric layer overlying the plate below the control electrode, the electron-emissive element situated mostly in an opening through the dielectric layer.
- 64. (Original) A structure as in Claim 61 further including a raised section overlying the plate and extending over at least part of the control electrode, the electron-emissive element being exposed through a primary opening in the raised section.
- 65. (Original) A structure as in Claim 64 wherein the getter region is exposed through or/and situated in the primary opening in the raised section.
- 66. (Original) A structure as in Claim 65 wherein the getter region comprises electrically non-insulating material electrically coupled to the control electrode.
- 67. (Original) A structure as in Claim 66 wherein the raised section comprises electrically non-insulating material substantially electrically decoupled from both the control electrode and the non-insulating material of the getter region.
- 68. (Original) A structure as in Claim 64 wherein the getter region is exposed through or/and situated in a further opening in the raised section, no operable electron-emissive element being exposed through the further opening in the raised section.
- 69. (Previously amended) A structure as in Claim 68 wherein the getter region comprises electrically non-insulating material substantially electrically decoupled from the control electrode.
- 70. (Canceled)
- 71. (Original) A structure as in Claim 69 wherein the raised section comprises electrically non-insulating material electrically coupled to the non-insulating material of the getter region.
- 72. (Original) A structure as in Claim 64 wherein the raised section comprises an electron-focusing system for focusing electrons emitted by the electron-emissive element.

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- 73. (Original) A structure as in Claim 61 wherein the getter region focuses electrons emitted by the electron-emissive element.
- 74. (Original) A structure as in Claim 73 wherein the getter region comprises electrically non-insulating material substantially electrically decoupled from the control electrode.
- 75. (Canceled)
- 76. (Original) A structure as in Claim 61 further including a device for emitting light upon being struck by electrons emitted by the electron-emissive element.
- 77. (Previously amended) A structure as in Claim 76 wherein the light-emitting device includes a further getter region situated at least partially in an active light-emitting portion of the light-emitting device.
- 78 83. (Canceled)
- 84. (Previously amended) A structure comprising:
  - a plate;
  - a group of electron-emissive elements overlying the plate;
- a group of laterally separated control electrodes for selectively extracting electrons from the electron-emissive elements or for selectively passing electrons emitted by the electron-emissive elements, the control electrodes overlying the plate, the electron-emissive elements being exposed through respective openings in the control electrodes; and
- a getter region overlying the plate at least partially between a consecutive pair of the control electrodes.
- 85. (Original) A structure as in Claim 84 wherein the getter region comprises electrically non-insulating material electrically coupled to no more than one of the control electrodes.
- 86. (Original) A structure as in Claim 84 wherein the getter region comprises electrically non-insulating material largely electrically decoupled from each control electrode.

- 87. (Original) A structure as in Claim 84 wherein the getter region is connected by directly underlying material to the plate.
- 88. (Previously amended) A structure as in Claim 84 further including a raised section overlying the plate and extending over at least part of each control electrode, the electron-emissive elements also being exposed through respective openings in the raised section, the getter region being exposed through or/and situated in an opening in the raised section.
- 89. (Original) A structure as in Claim 88 wherein the raised section comprises an electron-focusing system for focusing electrons emitted by the electron-emissive elements.
- 90. (Original) A structure as in Claim 89 wherein the raised section further includes an additional getter region situated over at least part of an electrically non-insulating base focusing structure of the electron-focusing system.
- 91. (Original) A structure as in Claim 84 further including a dielectric layer overlying the plate, the electron-emissive elements being situated mostly in respective laterally separated openings in the dielectric layer, the control electrodes and getter region overlying the dielectric layer.
- 92. (Original) A structure as in Claim 91 further including an electrically conductive intermediate region situated between at least part of the dielectric layer and at least part of the getter region.
- 93. (Original) A structure as in Claim 92 further including a raised section overlying at least part of the dielectric layer and extending over at least part of each control electrode, the electron-emissive elements being exposed through respective openings in the raised section, the getter region being exposed through or/and situated in an additional opening in the raised section.
- 94. (Previously amended) A structure as in Claim 84 further including a device for emitting light upon being struck by electrons emitted by the electron-emissive elements.

- 95. (Previously amended) A structure as in Claim 94 wherein the light-emitting device includes a further getter region situated at least partially in an active light-emitting portion of the light-emitting device.
- 96. (Previously amended) A structure as in Claim 84 wherein the getter region comprises at least one of aluminum, titanium, vanadium, iron, zirconium, niobium, molybdenum, barium, tantalum, tungsten, and thorium.
- 97. (Previously amended) A structure as in Claim 84 wherein the getter region consists largely of only a single atomic element.
- 98. (Previously amended) A structure as in Claim 84 wherein the single atomic element is one of aluminum, titanium, vanadium, iron, zirconium, niobium, molybdenum, barium, tantalum, tungsten, and thorium.
- 99. (Original) A structure comprising:
  - a plate;
  - a group of electron-emissive elements overlying the plate;
- a group of laterally separated control electrodes for selectively extracting electrons from the electron-emissive elements or for selectively passing electrons emitted by the electron-emissive elements, the control electrodes overlying the plate;
- a raised section overlying the plate and extending over at least part of each control electrode; and
- a getter region overlying the plate and exposed through or/and situated in a primary opening in the raised section.
- 100. (Original) A structure as in Claim 99 wherein the electron-emissive elements are exposed through (a) respective openings through the control electrodes and (b) respective further openings through the raised section, one of the further openings in the raised section potentially being the primary opening in the raised section.
- 101. (Original) A structure as in Claim 99 wherein the getter region overlies at least part of a specified one of the control electrodes.

- 102. (Original) A structure as in Claim 101 wherein one of the electron-emissive elements is exposed through the primary opening in the raised section.
- 103. (Original) A structure as in Claim 101 wherein the getter region comprises electrically non-insulating material electrically coupled to the specified control electrode.
- 104. (Original) A structure as in Claim 103 wherein the raised section comprises electrically non-insulating material substantially electrically decoupled from both the control electrodes and the non-insulating material of the getter region.
- 105. (Original) A structure as in Claim 101 wherein no operable electron-emissive element is exposed through the opening in the raised section.
- 106. (Original) A structure as in Claim 105 wherein the getter region comprises electrically non-insulating material substantially electrically decoupled from the control electrodes.
- 107. (Previously amended) A structure as in Claim 106 further including an electrically insulating region situated between the getter region and the specified control electrode.
- 108. (Original) A structure as in Claim 106 wherein the raised section comprises electrically non-insulating material electrically coupled to the non-insulating material of the getter region.
- 109. (Original) A structure as in Claim 99 wherein the getter region overlies the plate at a location between where a consecutive pair of the control electrodes overlie the plate.
- 110. (Original) A structure as in Claim 109 further including a dielectric layer overlying the plate, the raised section, control electrodes, and getter region each overlying at least part of the dielectric layer.
- 111. (Original) A structure as in Claim 110 further including an intermediate electrically conductive region situated between at least part of the dielectric layer and at least part of the getter region.

- 112. (Original) A structure as in Claim 110 wherein the electron-emissive elements are (a) mostly situated in respective openings in the dielectric layer, (b) exposed through respective openings in the control electrodes, and (c) exposed through respective openings in the raised section.
- 113. (Original) A structure as in Claim 99 wherein the raised section comprises an electron-focusing system for focusing electrons emitted by the electron-emissive elements.
- 114. (Previously amended) A structure comprising:
  - a plate;
  - a dielectric layer overlying the plate;
- a group of electron-emissive elements overlying the plate and situated mostly in respective laterally separated openings in the dielectric layer; and
- a getter region overlying at least part of the dielectric layer and contacting, or connected by directly underlying electrically non-insulating material to, the dielectric layer, at least part of the getter region situated above a location between a pair of the openings in the dielectric layer.
- 115. (Original) A structure as in Claim 114 wherein the getter region focuses electrons emitted by the electron-emissive elements.
- 116. (Original) A structure as in Claim 114 further including a group of laterally separated control electrodes for selectively extracting electrons respectively from the electron-emissive elements or for selectively passing electrons emitted respectively by the electron-emissive elements, at least part of each control electrode overlying the dielectric layer, the electron-emissive elements being exposed through respective openings in the control electrodes.

117. (Previously amended) A structure as in Claim 116 further including a raised section overlying at least part of the dielectric layer and extending over at least part of each control electrode, the electron-emissive elements also being exposed through respective openings in the raised section.

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- 118. (Original) A structure as in Claim 117 wherein the getter region overlies at least part of a support region of the raised section.
- 119. (Original) A structure as in Claim 117 wherein the support region comprises a base focusing structure of an electron-focusing system for focusing electrons emitted by the electron-emissive elements, the electron-focusing system including an electrically non-insulating focus coating which comprises, overlies at least part of, or underlies at least part of the getter region.
- 120. (Original) A structure as in Claim 116 wherein the getter region overlies the dielectric layer at a location between a consecutive pair of the control electrodes.
- 121. (Original) A structure as in Claim 120 further including a raised section overlying at least part of the dielectric layer and extending over at least part of each control electrode, the electron-emissive elements being exposed through respective primary openings in the raised section, the getter region also being exposed through or/and situated in a further opening in the raised section, the further opening in the raised section potentially being one of the primary openings in the raised section.
- 122. (Original) A structure as in Claim 121 further including an electrically conductive intermediate region situated between at least part of the dielectric layer and at least part of the getter region.
- 123. (Original) A structure as in Claim 116 wherein the getter region is situated over at least part of one of the control electrodes.
- 124. (Original) A structure as in Claim 123 further including a raised section overlying at least part of the dielectric layer and extending over at least part of each control electrode, the electron-emissive elements being exposed through respective openings in the raised section, the getter region being exposed through or/and situated in the raised section's opening that exposes the electron-emissive element also exposed through the opening in the control electrode which the getter region overlies.

- 125. (Original) A structure as in Claim 116 wherein the getter region focuses electrons emitted by the electron-emissive elements.
- 126. (Original) A structure as in Claim 125 wherein the getter region comprises electrically non-insulating material substantially electrically decoupled from the control electrode.

127 - 265. (Canceled)

- 266. (Previously presented) A structure as in Claim 31 wherein the getter region comprises at least one of aluminum, titanium, vanadium, iron, zirconium, niobium, molybdenum, barium, tantalum, tungsten, and thorium.
- 267. (Previously presented) A structure as in Claim 61 wherein the getter region comprises at least one of aluminum, titanium, vanadium, iron, zirconium, niobium, molybdenum, barium, tantalum, tungsten, and thorium.

268 - 270. (Canceled)

- 271. (Previously presented) A structure as in Claim 84 wherein the getter region overlies the plate at least partially between at least one other consecutive pair of the control electrodes.
- 272. (Previously presented) A structure as in Claim 271 further including a light-emitting device having an active light-emitting portion comprising a like multiplicity of laterally separated light-emissive regions situated generally opposite the electron-emissive regions, each light-emissive region emitting light upon being struck by electrons emitted by the oppositely situated electron-emissive region.
- 273. (Previously presented) A structure as in Claim 272 wherein the light-emitting device includes a further getter region situated at least partially in, and distributed across, the active light-emitting portion.

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- 274. (Previously presented) A structure as in Claim 99 wherein the getter region comprises at least one of aluminum, titanium, vanadium, iron, zirconium, niobium, molybdenum, barium, tantalum, tungsten, and thorium.
- 275. (Previously presented) A structure as in Claim 99 further including a device for emitting light upon being struck by electrons emitted by the electron-emissive element.
- 276. (Previously presented) A structure as in Claim 275 wherein the light-emitting device includes a further getter region situated at least partially in an active light-emitting portion of the light-emitting device.
- 277. (Previously presented) A structure as in Claim 99 wherein the getter region is exposed through or/and situated in at least one other primary opening in the raised section.
- 278. (Previously presented) A structure as in Claim 277 further including a light-emitting device having an active light-emitting portion comprising a like multiplicity of laterally separated light-emissive regions situated generally opposite the electron-emissive regions, each light-emissive region emitting light upon being struck by electrons emitted by the oppositely situated electron-emissive region.
- 279. (Previously presented) A structure as in Claim 278 wherein the light-emitting device includes a further getter region situated at least partially in, and distributed across, the active light-emitting portion.
- 280. (Previously presented) A structure as in Claim 109 wherein the getter region overlies the plate at at least one location between where another pair of the control electrodes overlie the plate.
- 281. (Previously presented) A structure as in Claim 114 wherein the getter region comprises at least one of aluminum, titanium, vanadium, iron, zirconium, niobium, molybdenum, barium, tantalum, tungsten, and thorium.
- 282. (Previously presented) A structure as in Claim 114 further including a device for emitting light upon being struck by electrons emitted by the electron-emissive element.

- 283. (Previously presented) A structure as in Claim 282 wherein the light-emitting device includes a further getter region situated at least partially in an active light-emitting portion of the light-emitting device.
- 284. (Previously presented) A structure as in Claim 114 wherein the getter region is situated above at least one location between another pair of openings in the dielectric layer.
- 285. (Previously presented) A structure as in Claim 284 further including a light-emitting device having an active light-emitting portion comprising a like multiplicity of laterally separated light-emissive regions situated generally opposite the electron-emissive regions, each light-emissive region emitting light upon being struck by electrons emitted by the oppositely situated electron-emissive region.
- 286. (Previously presented) A structure as in Claim 285 wherein the light-emitting device includes a further getter region situated at least partially in, and distributed across, the active light-emitting portion.
- 287. (Previously presented) A structure as in Claim 120 where the getter region overlies the dielectric layer at at least one location between another consecutive pair of the control electrodes.
- 288. (Previously presented) A structure as in Claim 123 wherein the getter region is situated over at least part of another of the control electrodes.
- 289. (Previously presented) A structure comprising:
  - a plate;
- a light-blocking region overlying the plate and being generally non-transmissive of visible light, a multiplicity of openings extending largely through the light-blocking region above where the plate is generally transmissive of visible light;
- a like multiplicity of laterally separated light-emissive regions overlying the plate, each light-emissive region situated at least partially in a different corresponding one of the openings in the light-blocking region;

a getter region overlying at least part of the light-blocking region and extending no more than partially laterally across each light-emissive region such that material of the getter region overlies the light-blocking region above locations between pairs of adjacent ones of the light-emissive regions; and

a perforated electrically non-insulating layer overlying at least part of the getter region or/and at least part of each light-emissive region.

- 290. (Previously presented) A structure as in Claim 289 wherein a like multiplicity of openings extend through the getter region respectively generally laterally where the light-emissive regions overlie the plate.
- 291. (Previously presented) A structure as in Claim 289 wherein the light-blocking region is largely absorptive of visible light which passes through the plate and impinges on the light-blocking region.
- 292. (Previously presented) A structure as in Claim 289 wherein the non-insulating layer is electrically conductive.
- 293. (Previously presented) A structure as in Claim 289 wherein the non-insulating layer overlies at least part of each light light-emitting region.
- 294. (Previously presented) A structure as in Claim 293 wherein the non-insulating layer is generally reflective of visible light.
- 295. (Previously presented) A structure as in Claim 289 wherein the non-insulating layer overlies the getter and light-emissive regions.
- 296. (Previously presented) A structure as in Claim 289 wherein the light-blocking region laterally surrounds each light emitting region.
- 297. (Previously presented) A structure as in Claim 289 wherein the getter region comprises at least one of aluminum, titanium, vanadium, iron, zirconium, niobium, molybdenum, barium, tantalum, tungsten, and thorium.

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- 298. (Previously presented) A structure as in Claim 289 further including an additional region situated over at least part of the light-blocking region and under at least part of the non-insulating layer.
- 299. (Previously presented) A structure as in Claim 298 wherein the additional region is situated over at least part of the getter region.
- 300. (Previously presented) A structure as in Claim 298 wherein the additional region is largely impervious to passage of gases.
- 301. (Previously presented) A structure as in Claim 298 wherein the additional region is largely impervious to passage of electrons.
- 302. (Previously presented) A structure as in Claim 298 wherein the additional region covers all, or nearly all, of the light-blocking region along its outside surface.
- 303. (Previously presented) A structure as in Claim 289 further including a protective layer situated over at least part of the getter region and under the non-insulating layer, the protective layer lying between at least part of the getter region and at least part of the light-emissive region.
- 304. (Previously presented) A structure as in Claim 303 wherein the protective layer is largely impervious to passage of electrons.
- 305. (Previously presented) A structure as in Claim 289 wherein the light-blocking region has a remote surface most distant from the plate, the getter region overlying at least part of the remote surface of the light-blocking region.
- 306. (Previously presented) A structure as in Claim 289 wherein the getter region extends at least partway down into each opening in the light-blocking region.
- 307. (Previously presented) A structure as in Claim 289 wherein the getter region extends into each opening in the light-blocking region and partially over the plate at the bottom of each opening in the light-blocking region.

- 308. (Previously presented) A structure as in Claim 289 further including an electron-emitting device having an active electron-emitting portion which comprises a like multiplicity of laterally separated electron-emissive regions situated respectively generally opposite the light-emissive regions, each electron-emissive region being operable to emit electrons which strike the oppositely situated light-emissive region and cause it to emit light.
- 309. (Previously presented) A structure as in Claim 308 wherein the electron-emitting device includes a further getter region situated at least partially in, and distributed across, the active electron-emitting portion.
- 310. (Previously presented) A structure comprising:

a plate;

- a light-blocking region overlying the plate and being generally non-transmissive of visible light, a multiplicity of openings extending largely through the light-blocking region above where the plate is generally transmissive of visible light;
- a like multiplicity of laterally separated light-emissive regions overlying the plate, each light-emissive region situated at least partially in a different corresponding one of the openings in the light-blocking region;

an electrically non-insulating layer overlying at least part of the light-blocking region; and

- a getter region overlying at least part of the non-insulating layer above the light-blocking region, a like multiplicity of openings extending largely through the getter region respectively generally laterally where the light-emissive regions overlie the plate such that material of the getter region overlies the non-insulating region above locations between pairs of adjacent ones of the light-emissive regions.
- 311. (Previously presented) A structure as in Claim 310 wherein the light-blocking region is largely absorptive of visible light which passes through the plate and impinges on the light-blocking region.
- 312. (Previously presented) A structure as in Claim 311 wherein the non-insulating layer is electrically conductive.

Ronald J. Meetin Attorney at Law 210 Central Avenue Mountain View, CA 94043-4869

- 313. (Previously presented) A structure as in Claim 310 wherein the non-insulating layer overlies at least part of each light light-emitting region.
- 314. (Previously presented) A structure as in Claim 313 wherein the non-insulating layer is generally reflective of visible light.
- 315. (Previously presented) A structure as in Claim 310 wherein the light-blocking region laterally surrounds each light-emissive region.
- 316. (Previously presented) A structure as in Claim 310 wherein the getter region comprises at least one of aluminum, titanium, vanadium, iron, zirconium, niobium, molybdenum, barium, tantalum, tungsten, and thorium.
- 317. (Previously presented) A structure as in Claim 310 further including an electron-emitting device having an active electron-emitting portion which comprises a like multiplicity of laterally separated electron-emissive regions situated respectively generally opposite the light-emissive regions, each electron-emissive region being operable to emit electrons which strike the oppositely situated light-emissive region and cause it to emit light.
- 318. (Previously presented) A structure as in Claim 317 wherein the electron-emitting device includes a further getter region situated at least partially in, and distributed across, the active electron-emitting portion.
- 319. (Previously presented) A structure comprising:
  - a plate;
  - a multiplicity of laterally separated electron-emissive regions overlying the plate;
  - a support region overlying the plate; and
- a getter region overlying at least part of the support region, a multiplicity of composite openings extending through the getter and support regions generally laterally where the electron-emissive regions overlie the plate, each composite opening comprising (a) an opening through the getter region and (b) an opening through the support region such that material of the getter region overlies the support region above locations between pairs of adjacent electron-emitting regions.

- 320. (Previously presented) A structure as in Claim 319 further including a dielectric layer overlying the plate below the support region, the electron-emissive regions comprising electron-emissive elements situated mostly in openings in the dielectric layer.
- 321. (Previously presented) A structure as in Claim 319 further including a group of laterally separated control electrodes for selectively extracting electrons from the electron-emissive regions or for selectively passing electrons emitted by the electron-emissive regions, each control electrode overlying the plate and having a plurality of openings through which a like plurality of the electron-emissive regions are respectively exposed.
- 322. (Previously presented) A structure as in Claim 321 further including electrically insulating material extending over at least part of each control electrode.
- 323. (Previously presented) A structure as in Claim 319 wherein the support region comprises a base focusing structure of an electron-focusing system for focusing electrons emitted by the electron-emissive regions.
- 324. (Previously presented) A structure as in Claim 323 wherein the electron-focusing system includes an electrically non-insulating focus coating which comprises the getter region, whereby at least part of the focus coating overlies the base focusing structure.
- 325. (Previously presented) A structure as in Claim 323 wherein the electron-focusing system includes an electrically non-insulating focus coating situated over at least part of the getter region, a like multiplicity of openings extending through the focus coating at least generally laterally where the electron-emissive regions respectively overlie the plate.
- 326. (Previously presented) A structure as in Claim 325 wherein the focus coating is perforated.
- 327. (Previously presented) A structure as in Claim 323 wherein the electron-focusing system includes an electrically non-insulating focus coating situated over at least part of the base focusing structure and under at least part of the getter region.

- 328. (Previously presented) A structure as in Claim 319 wherein the support region comprises a group of laterally separated control electrodes for selectively extracting electrons from the electron-emissive regions or for selectively passing electrons emitted by the electron-emissive regions.
- 329. (Previously presented) A structure as in Claim 328 further including a raised section overlying the plate and extending over at least part of each control electrode, the getter region being exposed through or/and situated in a plural number of openings in the raised section.
- 330. (Previously presented) A structure as in Claim 329 wherein the getter region comprises plural laterally separated getter portions.
- 331. (Previously presented) A structure as in Claim 328 wherein the getter region focuses electrons emitted by the electron-emissive regions.
- 332. (Previously presented) A structure as in Claim 331 wherein the getter region comprises electrically non-insulating material substantially electrically decoupled from the control electrodes.
- 333. (Previously presented) A structure as in Claim 319 wherein the getter region comprises at least one of aluminum, titanium, vanadium, iron, zirconium, niobium, molybdenum, barium, tantalum, tungsten, and thorium.
- 334. (Previously presented) A structure as in Claim 319 wherein each electron-emissive region comprises multiple electron-emissive elements.
- 335. (Previously presented) A structure as in Claim 319 further including a light-emitting device having an active light-emitting portion comprising a like multiplicity of laterally separated light-emissive regions situated generally opposite the electron-emissive regions, each light-emissive region emitting light upon being struck by electrons emitted by the oppositely situated electron-emissive region.

- 336. (Previously presented) A structure as in Claim 335 wherein the light-emitting device includes a further getter region situated at least partially in, and distributed across, the active light-emitting portion.
- 337. (Previously presented) A structure comprising: a plate;
  - a multiplicity of laterally separated electron-emissive regions overlying the plate;
- a group of laterally separated control electrodes for selectively extracting electrons from the electron-emissive regions or for selectively passing electrons emitted by the electron-emissive regions, each control electrode overlying the plate and having a plurality of openings through which a like plurality of the electron-emissive regions are exposed; and
- a getter region overlying at least part of each control electrode and contacting, or connected by directly underlying electrically insulating material to, each control electrode.
- 338. (Previously presented) A structure as in Claim 337 wherein a like multiplicity of openings extend through the getter region generally laterally where the electron-emissive regions respectively overlie the plate.
- 339. (Previously presented) A structure as in Claim 337 further including a dielectric layer overlying the plate below the control electrodes, the electron-emissive regions comprising electron-emissive elements situated mostly in openings through the dielectric layer.
- 340. (Previously presented) A structure as in Claim 337 further including a raised section overlying the plate and extending over at least part of each control electrode, a like multiplicity of primary openings extending through the raised section to respectively expose the electron-emissive regions.
- 341. (Previously presented) A structure as in Claim 340 wherein the getter region is exposed through or/and situated in the primary openings in the raised section.
- 342. (Previously presented) A structure as in Claim 341 wherein the getter region comprises multiple laterally separated electrically non-insulating getter portions, each electrically coupled to only one of the control electrodes.

- 343. (Previously presented) A structure as in Claim 342 wherein the raised section comprises electrically non-insulating material substantially electrically decoupled from both the control electrodes and the getter portions.
- 344. (Previously presented) A structure as in Claim 340 wherein the getter region is exposed through or/and situated in multiple further openings in the raised section, no operable electron-emissive region being exposed through any of the further openings in the raised section.
- 345. (Previously presented) A structure as in Claim 344 wherein the getter region comprises multiple laterally separated electrically non-insulating getter portions, each exposed through or/and situated in at least one of the further openings in the raised section.
- 346. (Previously presented) A structure as in Claim 345 wherein each getter portion is substantially electrically decoupled from each control electrode.
- 347. (Previously presented) A structure as in Claim 346 wherein the raised section comprises electrically non-insulating material electrically coupled to the getter portions.
- 348. (Previously presented) A structure as in Claim 340 wherein the raised section comprises an electron-focusing system for focusing electrons emitted by the electron-emissive regions.
- 349. (Previously presented) A structure as in Claim 337 wherein the getter region focuses electrons emitted by the electron-emissive regions.
- 350. (Previously presented) A structure as in Claim 337 wherein the getter region comprises electrically non-insulating material substantially electrically decoupled from the control electrodes.
- 351. (Previously presented) A structure as in Claim 337 wherein the getter region comprises at least one of aluminum, titanium, vanadium, iron, zirconium, niobium, molybdenum, barium, tantalum, tungsten, and thorium.

- 352. (Previously presented) A structure as in Claim 337 wherein each electron-emissive region comprises multiple electron-emissive elements.
- 353. (Previously presented) A structure as in Claim 337 further including a light-emitting device having an active light-emitting portion comprising a like multiplicity of laterally separated light-emissive regions situated generally opposite the electron-emissive regions, each light-emissive region emitting light upon being struck by electrons emitted by the oppositely situated electron-emissive region.
- 354. (Previously presented) A structure as in Claim 353 wherein the light-emitting device includes a further getter region situated at least partially in, and distributed across, the active light-emitting portion.
- 355. (Previously presented) A structure comprising: a plate;
- a multiplicity of laterally separated electron-emissive regions overlying the plate; and a getter region overlying the plate, a like multiplicity of openings extending through the getter region to respectively expose the electron-emissive regions, the getter region being shaped, positioned, and controlled to focus electrons emitted by the electron-emissive
- 356. (Previously presented) A structure as in Claim 355 wherein the getter region receives a focus potential.
- 357. (Previously presented) A structure as in Claim 355 further including a group of laterally separated control electrodes for selectively extracting electrons emitted by the electron-emissive regions or for selectively passing electrons emitted by the electron-emissive regions, each control electrode overlying the plate and having a plurality of openings through which a like plurality of the electron-emissive regions are respectively exposed.

regions.

- 358. (Previously presented) A structure as in Claim 357 wherein the getter region comprises electrically non-insulating material substantially electrically decoupled from the control electrodes.
- 359. (Previously presented) A structure as in Claim 358 further including an electrically insulating layer overlying at least part of each control electrode, the getter region overlying at least part of the insulating layer and being of greater average thickness than the insulating layer.
- 360. (Previously presented) A structure as in Claim 355 wherein the getter region comprises an electrically insulating base focusing structure and an electrically non-insulating focus coating that overlies the base focusing structure.
- 361. (Previously presented) A structure as in Claim 355 wherein the getter region comprises at least one of aluminum, titanium, vanadium, iron, zirconium, niobium, molybdenum, barium, tantalum, tungsten, and thorium.
- 362. (Previously presented) A structure as in Claim 355 wherein each electron-emissive region comprises multiple electron-emissive elements.
- 363. (Previously presented) A structure as in Claim 355 further including a light-emitting device having an active light-emitting portion comprising a like multiplicity of laterally separated light-emissive regions situated generally opposite the electron-emissive regions, each light-emissive region emitting light upon being struck by electrons emitted by the oppositely situated electron-emissive region.
- 364. (Previously presented) A structure as in Claim 363 wherein the light-emitting device includes a further getter region situated at least partially in, and distributed across, the active light-emitting portion.